


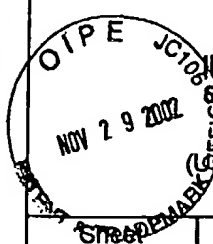
<div style="text-align: center;">  <p><b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> Form PTO-1449 (Modified) Use several sheets if necessary)</p> </div>				<b>COMPLETE IF KNOWN</b>	
				Application Number	09/885,451
				Confirmation Number	3390
				Filing Date	June 20, 2001
				First Named Inventor	Thomas Ritzdorf
				Group Art Unit	1742
Examiner Name	Leader, William T.				
Attorney Docket No.	29195-8170US2				
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U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No.	U.S. Patent or Application		Name of Patentee or Inventor of Cited Document	Date of Publication or Filing Date of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		NUMBER	Kind Code (if known)			
WL		3,715,289		Cope, Jr.	02/06/73	
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WL		5,989,623		Chen et al.	11/23/99	
WL		6,066,892		Ding et al.	05/23/00	

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WL		TOMOV, I.V. et al. "Recovery and recrystallization of electrodeposited bright copper coatings at room temperature. II. X-ray investigation of primary recrystallization," Journal of Applied Electrochemistry, 1985, pp 887-894, Vol 15, Chapman and Hall Ltd.	
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		Office	NUMBER	Kind Code (if known)				
WL		EP	*0 751 567 A2		Intl. Business Machines Corp.	01/02/97		
WL		EP	*0 881 672 A2		Intl. Business Machines Corp.	12/02/98		
WL		EP	*0 982 771 A1		Lucent Technologies, Inc.	03/01/00		
WL		WO	*98/27585		Intl. Business Machines Corp.	06/25/98		

OTHER PRIOR ART-NON PATENT LITERATURE DOCUMENTS

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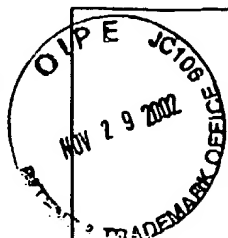
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WL		*TOMOV, V., STOYCHEV, D.S., VITANOVA, I.B., "Recovery And Recrystallization Of Electrodeposited Bright Copper Coatings At Room Temperature. II. X-Ray Investigation Of Primary Recrystallization," <i>Journal of Applied Electrochemistry</i> , 15, 887-894. Chapman and Hall Ltd. (1985).	
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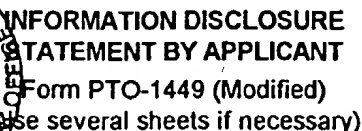
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W2		*WONG, C.C., SMITH, H.I., and THOMPSON, C.V., "Room Temperature Grain Growth in Thin Au Films, from <i>Grain Boundary Structure and Related Phenomena</i> , supplement to <i>Transactions of Japanese Institute of Metals</i> , 27, p. 641 (1986).	
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